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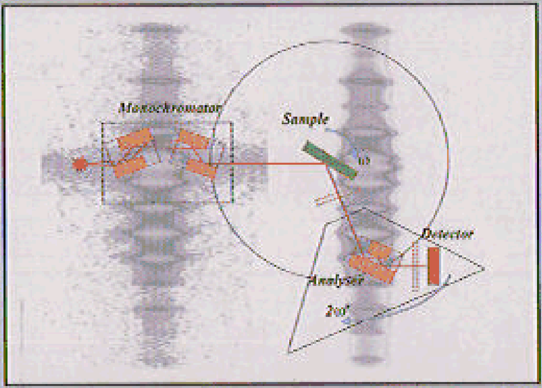

X-ray Scattering from Semiconductors

2nd Edition

Imperial College Press

Contents

Chapter 1
An Introduction to Semiconductor Materials

1.1. General outline
1.2. Semiconductors 2
1.3. Method 6
1.4. Properties of X-rays 8
1.5. Instrumentation 11
1.6. Sample definition 12
References 21

Chapter 2
An Introduction to X-Ray Scattering

2.1. The interaction of X-ray photons with the sample 23
2.2. The nature of the scattered X-ray photon with no energy loss 25
2.3. The near exact theoretical description of scattering 33
    2.3.1. The condition of a single wave generated in a crystal 43
    2.3.2. The condition of two waves generated in a crystal 45
    2.3.3. A further discussion on the deviation parameter β_H 53
2.4. A scattering theory to accommodate real crystals 56
2.5. Scattering theory for structures with defects 60
2.6. Scattering theory of reciprocal space maps 64
2.7. Approximate theory: The kinematical approach 68
    2.7.1. Comparison between dynamical and kinematical models of diffraction 68
    2.7.2. The important derivations of the kinematical theory 70
    2.7.3. Lateral dimension analysis 74
    2.7.4. Scattering by defects: Diffuse scattering 77
2.8. Optical theory applied to reflectometry 82
    2.8.1. Some general conclusions from this analysis 88
    2.8.2. Imperfect interfaces 90
2.9. In-plane scattering 96

2.10. Transmission geometry 99
2.11. General conclusions 102
References 103

Chapter 3
Equipment for Measuring Diffraction Patterns

3.1. General considerations 105
3.2. Basics of the resolution function 108
3.3. X-ray source 111
3.4. X-ray detectors 113
    3.4.1. The proportional detector 114
    3.4.2. The scintillation detector 117
    3.4.3. The solid state detector 118
    3.4.4. Position sensitive detectors 119
3.5. Incident beam conditioning with passive components 121
    3.5.1. Incident beam slits: Fixed arrangement 121
    3.5.2. Incident beam slits: Variable arrangement 124
    3.5.3. Parallel Plate Collimators 126
    3.5.4. General considerations of slits 127
3.6. Incident beam conditioning with active components 128
    3.6.1. Incident beam filters 128
    3.6.2. Incident beam single crystal conditioners 129
        3.6.2.1. Single crystal groove conditioners 130
    3.6.3. Multiple crystal monochromators 132
    3.6.4. Multilayer beam conditioners 136
    3.6.5. Beam pipes 138
3.7 Diffractometer options: Combinations with scattered beam analysers 140
    3.7.1. Single slit incident and scattered beam diffractometers 141
        3.7.1.1. Applications in reflectometry 143
    3.7.2. Enhancements to the single slit incident and scattered beam diffractometers 145
    3.7.3. Double slit incident and parallel plate collimator scattered beam diffractometers 146
        3.7.3.1. Enhanced double-slit incident and parallel-plate collimator scattered beam diffractometers 147

3.7.3.2. Applications for low-resolution in-plane scattering 147
3.7.4. Diffractometers using variable slit combinations 150
3.7.4.1. Applications in reflectometry 150
3.8. Scattered beam analysers with active components 151
3.8.1. The double crystal diffractometer 151
3.8.1.1. Alignment of high resolution diffractometers 152
3.8.1.2. Applications of the double crystal diffractmeter 154
3.8.2. The triple crystal diffractometer 154
3.8.2.1. Applications of the triple axis diffractometer 155
3.8.3. The multiple crystal diffractometer 155
3.8.3.1. General considerations of data collection 160
3.8.3.2. Alignment of multiple crystal diffractometers 161
3.8.3.3. Three dimensional reciprocal space mapping 164
3.8.3.4. Applications of multiple crystal diffractometry 166
3.8.3.5. In-plane scattering in very high resolution 167
3.9. General conclusions 169
References 170

Chapter 4
A Practical Guide to the Evaluation of Structural Parameters

4.1. General considerations 171
4.2. General principles 172
4.3. Analysis of bulk semiconductor materials 173
4.3.1. Orientation 174
4.3.1.1. Surface orientation – the Laue method 174
4.3.1.2. Determining the orientation by diffractometry 177
4.3.1.2.2. Monochromator and open detector method 177
4.3.1.2.3. Multiple crystal diffractometer method 179
4.3.1.3. Determining polar directions 180
4.3.2. Revealing the mosaic structure in a bulk sample 182
4.3.2.1. Mosaic samples with large tilts 182

4.3.2.2. High resolution scanning methods (Lang method) 184
4.3.2.3. Multiple crystal methods for revealing mosaic blocks 187
4.3.3. Characterising the surface quality 192
4.3.4. Measuring the absolute interatomic spacing in semiconductor materials 195
4.3.5. Measuring the curvature of crystalline and non-crystalline substrates 197
4.4. Analysis of nearly perfect semiconductor multi-layer structures 200
4.4.1. The first assumption and very approximate method in determining composition 200
4.4.2. The determination of thickness 205
4.4.2.1. Determining the thickness from the fringes close to main scattering peaks 205
4.4.2.2. Determining the thickness from the fringes in the reflectometry profile 208
4.4.3. The simulation of rocking curves to obtain composition and thickness 209
4.4.3.1. Example of an analysis of a nearly perfect structure 210
4.4.3.2. Direct analysis from peak separation and fringe separations 212
4.4.3.3. Simulation using an iterative adjustment of the model 212
4.4.3.3.1. Linking parameters to cope with complex multi-layer structures 213
4.4.3.4. Automatic fitting of the data by simulation 215
4.4.3.5. Data collection with the 2-crystal 4-reflection monochromator and 3-reflection analyser 219
4.4.3.6. Reciprocal space map to analyse the imperfections in samples 220
4.4.3.7. Taking account of tilts in rocking curve analyses 224
4.4.3.8. Modelling the extent of the interface disruption in relaxed structures 226

4.4.3.9. Detailed analysis to reveal alloy segregation and the full structure of a multi-layer 227
4.4.4. Analysis of periodic multi-layer structures 229
4.4.4.1. The analysis using direct interpretation of the scattering pattern 229
4.4.4.2. The analysis using basic kinematical theory 231
4.4.4.3. Analysis of periodic multi-layers with dynamical theory 235
4.4.4.4. Analysis of periodic structures with reflectometry 238
4.4.4.5. Analysis of a nearly perfect epitaxial periodic multi-layer 239
4.4.4.5.1. Analysis based on the kinematical approach 240
4.4.4.5.2. Analysis based on the optical theory with reflectometry 245
4.4.4.5.3. Analysis based on the dynamical theory simulation 247
4.5. Analysis of mosaic structures (textured epitaxy) 248
4.6. Analysis of partially relaxed multi-layer structures (textured epitaxy) 249
4.6.1. Measuring the state of strain in partially relaxed thin layers 251
4.6.2. Obtaining the composition in partially relaxed thin layers 253
4.6.3. The measurement of the degree of relaxation and mismatch in thin layers 255
4.6.4. The determination of relaxation and composition with various methods 256
4.6.4.1. Determination by reciprocal space maps on an absolute scale 256
4.6.4.2. Determination by using a series of rocking curves and analyser scans 258
4.6.4.3. Determination by reciprocal space maps on a relative scale 260
4.6.4.4. Determination by rocking curves alone 261
4.6.4.5. Revealing dislocations and defects by topography 263

4.6.4.6. Simulating structures with defects 264
4.7. Analysis of laterally inhomogeneous multi-layers (textured polycrystalline) 266
4.7.1. Direct analysis of laterally inhomogeneous multi-layers 266
4.7.2. Simulation of laterally inhomogeneous multi-layers 270
4.7.3. Lateral inhomogeneities without large misfits 272
4.7.3.1. Analysing epitaxial layers with very small twinned regions 273
4.7.3.2. Analysing twin components larger than 5 microns 274
4.8. Analysis of textured polycrystalline semiconductors 275
4.9. Analysis of nearly perfect polycrystalline materials 277
4.9.1. Measurement of thickness of CrO_x on glass 278
4.9.2. Analysis of very weak scattering 280
4.10. Concluding remarks 282
References 282

Appendix 1
General Crystallographic Relations

A.1. Introduction 285
A.2. Interplanar spacings 285
A.3. Stereographic projections 287

Subject Index 295